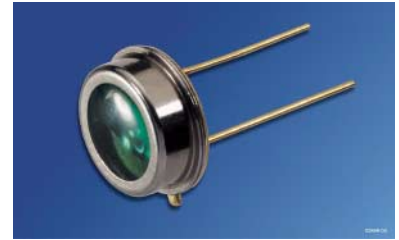


Silicon Photodiode for the Visible Spectral Range

Silicon Photodiode for the Visible Spectral Range

Lead (Pb) Free Product - RoHS Compliant

BPW 21



Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 350nm bis 820nm
- Angepaßt an die Augenempfindlichkeit (V_{λ})
- Hermetisch dichte Metallbauform (ähnlich TO-5)

Anwendungen

- Belichtungsmesser für Tageslicht
- Für Kunstlicht mit hoher Farbtemperatur in der Fotografie und Farbanalyse

Features

- Especially suitable for applications from 350nm to 820nm
- Adapted to human eye sensitivity (V_{λ})
- Hermetically sealed metal package (similar to TO-5)

Application

- Exposure meter for daylight
- For artificial light of high color temperature in photographic fields and color analysis

Typ Type	Bestellnummer Ordering Code
BPW 21	Q62702P0885

Grenzwerte**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 80	°C
Sperrspannung Reverse voltage	V_R	10	V
Verlustleistung, $T_A = 25\text{ °C}$ Total power dissipation	P_{tot}	250	mW

Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)**Characteristics** ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotoempfindlichkeit, $V_R = 5\text{ V}$ Spectral sensitivity	S	10 (≥ 5.5)	nA/lx
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\max}$	550	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{\max} Spectral range of sensitivity $S = 10\%$ of S_{\max}	λ	350 ... 820	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	7.34	mm ²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	2.73×2.73	mm × mm
Halbwinkel Half angle	φ	± 55	Grad deg.
Dunkelstrom $V_R = 10\text{ V}$ Dark current $V_R = 5\text{ V}$ $V_R = 10\text{ mV}$	I_R I_R	2 (≤ 30) 8 (≤ 200)	nA pA
Spektrale Fotoempfindlichkeit, $\lambda = 550\text{ nm}$ Spectral sensitivity	S_λ	0.34	A/W
Quantenausbeute, $\lambda = 550\text{ nm}$ Quantum yield	η	0.80	Electrons Photon
Leerlaufspannung, $E_v = 1000\text{ lx}$ Open-circuit voltage	V_O	400 (≥ 320)	mV

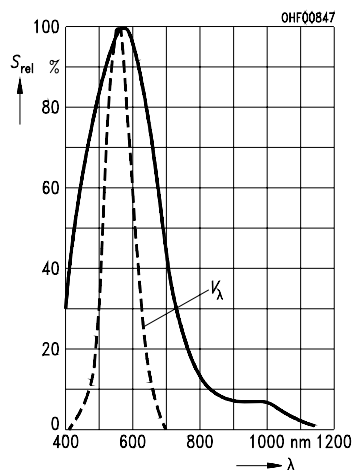
Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)

Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$) (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Kurzschlußstrom, $E_V = 1000\text{ lx}$ Short-circuit current	I_{SC}	10	μA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 1\text{ k}\Omega$; $V_R = 5\text{ V}$; $\lambda = 550\text{ nm}$; $I_p = 10\text{ }\mu\text{A}$	t_r, t_f	1.5	μs
Durchlaßspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.2	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	580	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	-2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC}	TC_I	-0.05	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 5\text{ V}$, $\lambda = 550\text{ nm}$	NEP	7.2×10^{-14}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 5\text{ V}$, $\lambda = 550\text{ nm}$ Detection limit	D^*	1×10^{12}	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

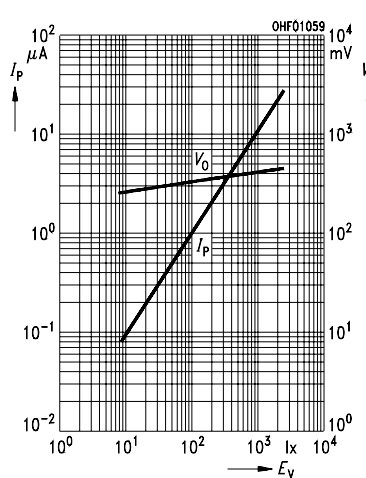
Relative Spectral Sensitivity

$S_{rel} = f(\lambda)$



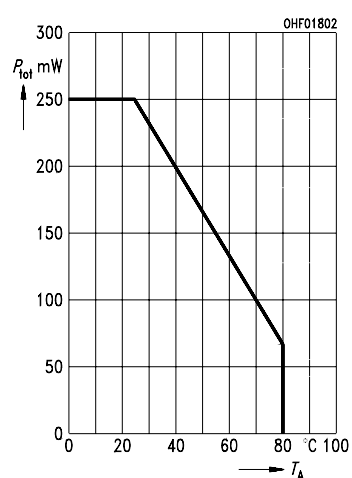
Photocurrent $I_P = f(E_V), V_R = 5 V$

Open-Circuit Voltage $V_O = f(E_V)$



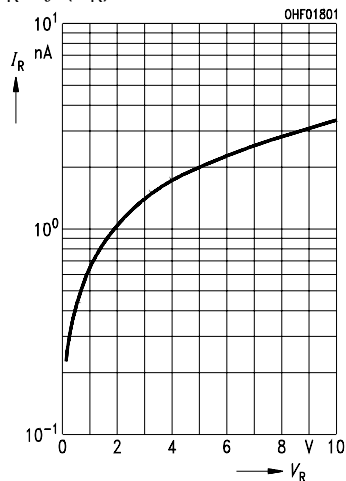
Total Power Dissipation

$P_{tot} = f(T_A)$



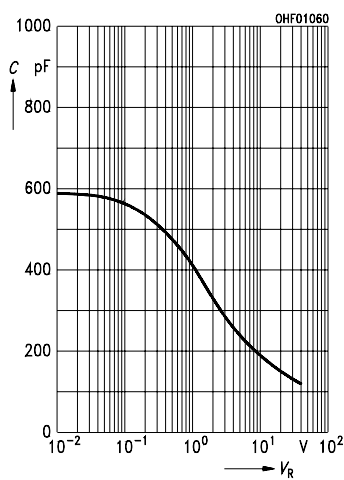
Dark Current

$I_R = f(V_R)$



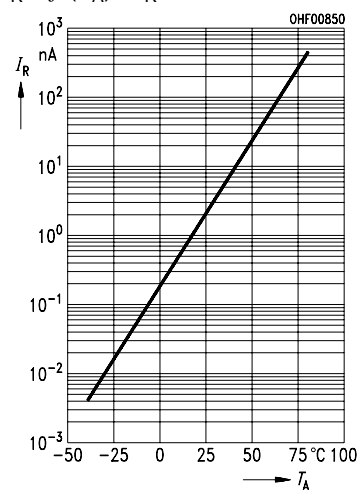
Capacitance

$C = f(V_R), f = 1 \text{ MHz}, E = 0$



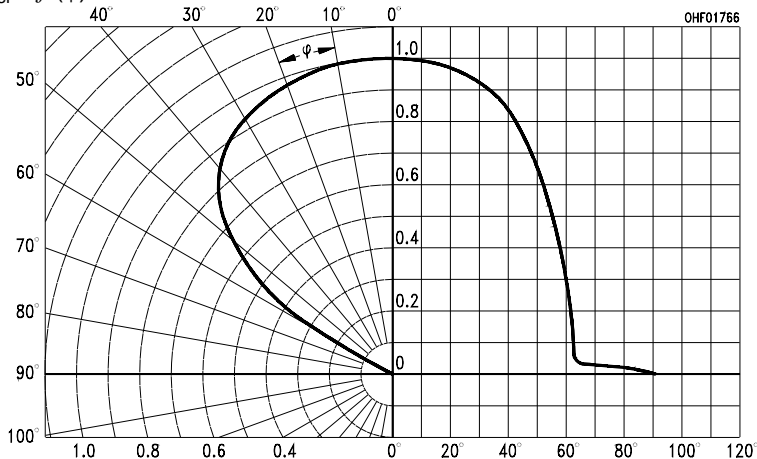
Dark Current

$I_R = f(T_A), V_R = 5 V$

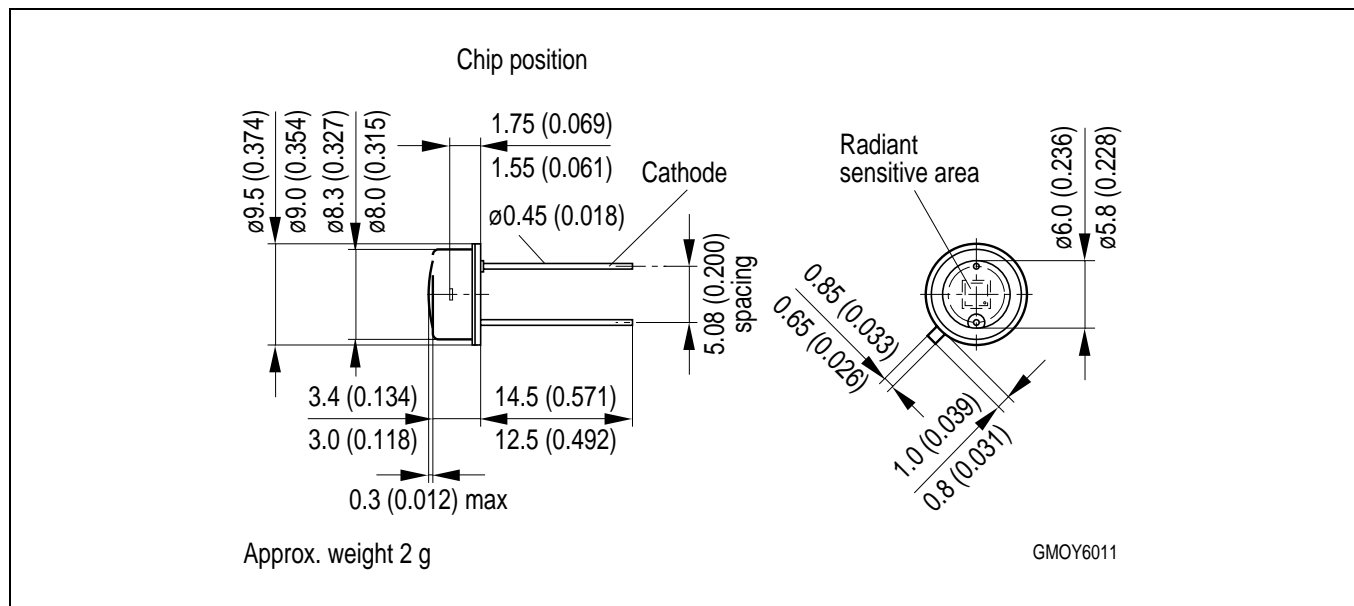


Directional Characteristics

$S_{rel} = f(\varphi)$



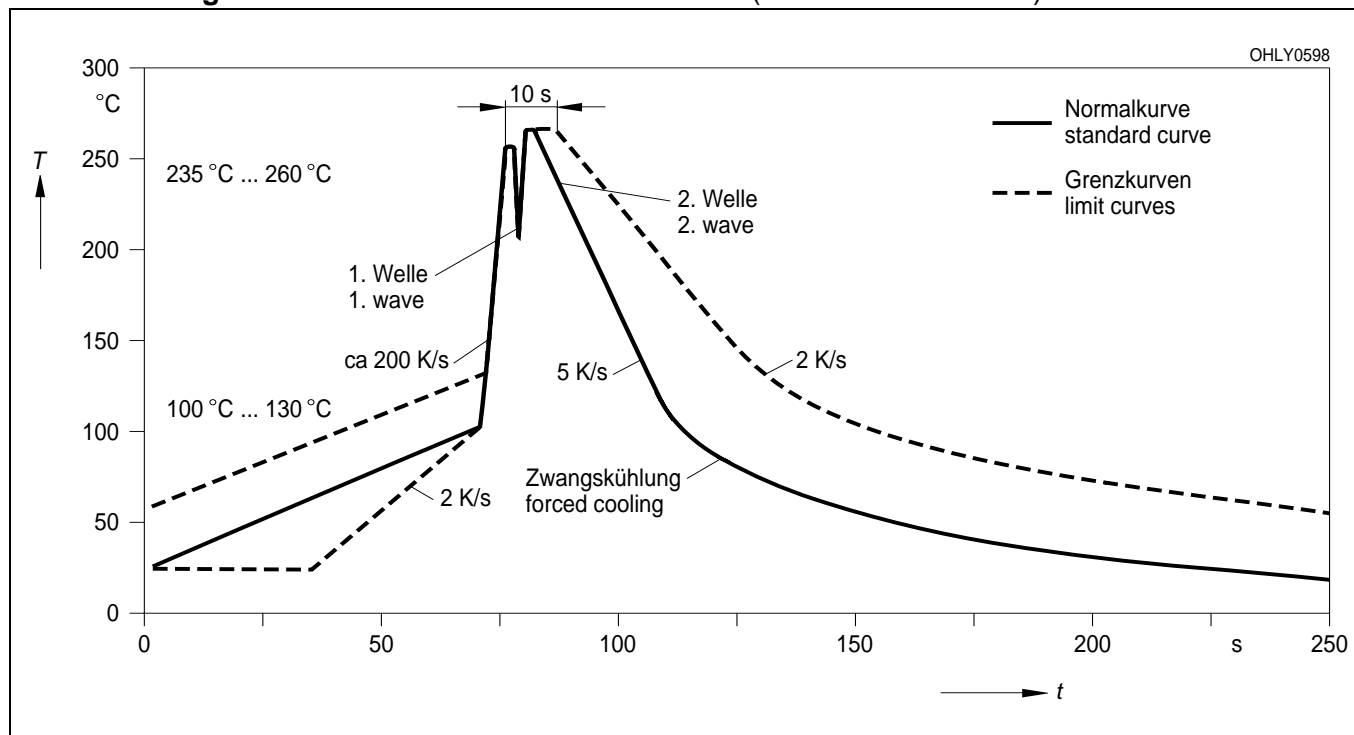
**Maßzeichnung
Package Outlines**



Maße in mm (inch) / Dimensions in mm (inch).

**Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering**

(nach CECC 00802)
(acc. to CECC 00802)



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¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

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EU RoHS and China RoHS compliant product



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